

JFW

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Shangjr Gwo : Attention:  
Serial No.: 10/714,649 : Office of Initial  
Filed : 18 November 2003 Patent Examination's  
Title : METHOD FOR GROWING GROUP-III : Filing Receipt Corrections  
NITRIDE SEMICONDUCTOR HETERO-  
STRUCTURE ON SILICON SUBSTRATE

REQUEST FOR CORRECTED FILING RECEIPT

Mail Stop NO FEE  
Honorable Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

The undersigned attorney has received the Official Filing Receipt for the above-referenced Patent Application. There are errors in the Official Filing Receipt as is highlighted on the attached copy. It is requested that the following errors be corrected.

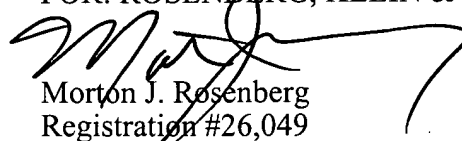
ERROR IN OFFICIAL FILING RECEIPT

The Applicant's Name is incorrect. Please correct the Applicant's Name to read: SHANGJR GWO. Attached is a copy of the originally filed Declaration for Patent Application showing the correct spelling of Applicant.

Please correct the Official Filing Receipt and send a Corrected Filing Receipt to the undersigned attorney.

Respectfully submitted,

FOR: ROSENBERG, KLEIN & LEE

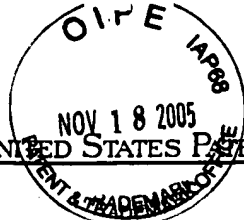


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Dated: 17 Nov 2005

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04586



## UNITED STATES PATENT AND TRADEMARK OFFICE

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APPL NO.	FILING OR 371 (c) DATE	ART UNIT	FIL FEE REC'D	ATTY. DOCKET NO	DRAWINGS	TOT CLMS	IND CLMS
10/714,649	11/18/2003	2812	554	MR3029-81	7	34	4

CONFIRMATION NO. 2517

04586  
 ROSENBERG, KLEIN & LEE  
 3458 ELLICOTT CENTER DRIVE-SUITE 101  
 ELLICOTT CITY, MD 21043

## FILING RECEIPT



\*OC000000012037204\*

Date Mailed: 03/05/2004

Receipt is acknowledged of this regular Patent Application. It will be considered in its order and you will be notified as to the results of the examination. Be sure to provide the U.S. APPLICATION NUMBER, FILING DATE, NAME OF APPLICANT, and TITLE OF INVENTION when inquiring about this application. Fees transmitted by check or draft are subject to collection. Please verify the accuracy of the data presented on this receipt. If an error is noted on this Filing Receipt, please write to the Office of Initial Patent Examination's Filing Receipt Corrections, facsimile number 703-746-9195. Please provide a copy of this Filing Receipt with the changes noted thereon. If you received a "Notice to File Missing Parts" for this application, please submit any corrections to this Filing Receipt with your reply to the Notice. When the USPTO processes the reply to the Notice, the USPTO will generate another Filing Receipt incorporating the requested corrections (if appropriate).

Applicant(s) **SHANGJR**  
 Shangir Gwo, Hsin-Chu City, TAIWAN;

Domestic Priority data as claimed by applicant

Foreign Applications

If Required, Foreign Filing License Granted: 03/05/2004

Projected Publication Date: 05/19/2005

Non-Publication Request: No

Early Publication Request: No

\*\* SMALL ENTITY \*\*

Title

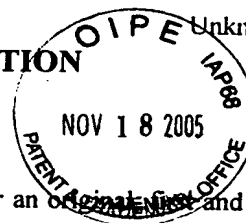
Method for growing group-III nitride semiconductor heterostructure on silicon substrate

Preliminary Class

438

# DECLARATION FOR PATENT APPLICATION

Unknown-US92122/P1



As a below named inventor, I hereby declare that:

My residence, post office address and citizenship are as stated below next to my name.

I believe I am the original, first and sole inventor (if only one name is listed below) or an original, first and joint inventor (if plural names are listed below) of the subject matter which is claimed and for which a patent is sought on the invention entitled METHOD FOR GROWING GROUP-III NITRIDE SEMICONDUCTOR HETEEROSTRUCTURE ON SILICON SUBSTRATE

The specification of which is attached hereto unless the following box is checked:

☐ was filed on \_\_\_\_\_ as United States Application Number or PCT International Application Number \_\_\_\_\_ and was amended on \_\_\_\_\_ (if applicable).

I hereby state that I have reviewed and understand the contents of the above identified specification, including the claims, as amended by any amendment referred to above.

I acknowledge the duty to disclose information which is material to patentability as defined in 37 CFR § 1.56.

I hereby claim foreign priority benefits under 35 U.S.C. § 119(a)-(d) or 365(b) of any foreign application(s) for patent or inventor's certificate, or § 365(a) of any PCT International application which designated at least one country other than the United States, listed below and have also identified below, by checking the box, any foreign application for patent or inventor's certificate, or PCT International application having a filing date before that of the application on which priority is claimed.

Priority Not Claimed



COPY

_____ (Number)	_____ (Country)	_____ (Day/Month/Year Filed)
_____ (Number)	_____ (Country)	_____ (Day/Month/Year Filed)

I hereby claim the benefit under 35 U.S.C. § 119(e) of any United States provisional application(s) listed below.

_____ (Application Number)	_____ (Filing Date)
_____ (Application Number)	_____ (Filing Date)

I hereby claim the benefit under 35 U.S.C. § 120 of any United States application(s), or § 365(c) of any PCT International application designating the United States, listed below and, insofar as the subject matter of each of the claims of this application is not disclosed in the prior United States or PCT International application in the manner provided by the first paragraph of 35 U.S.C. § 112.

I acknowledge the duty to disclose information which is material to patentability as defined in 37 CFR § 1.56 which became available between the filing date of the prior application and the national or PCT International filing date of this application.

_____ (Application Number)	_____ (Filing Date)	_____ (Status-patented, pending, abandoned)
_____ (Application Number)	_____ (Filing Date)	_____ (Status-patented, pending, abandoned)

I hereby appoint the following attorney(s) and/or agent(s) to prosecute this application and to transact all business in the Patent and Trademark Office connected therewith: MORTON J. ROSENBERG, ESQ., REG. #26,049; DAVID R. WOOD, #53,868;

HARRY L. SERNAKER, #50,595;

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I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code and that such willful false statements may jeopardize the validity of the application or any patent issued thereon.

Full name of sole or first inventor (given name, family name)  
Inventor's signature

Shangjr GWO (GWO IS FAMILY NAME)

Date

Nov. 10, 2003

Citizenship Taiwan R.O.C.

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